

SYD8811: Ultra Low Power Bluetooth Low Energy SoC

1.1 General Description

The SYD8811 is a low power and high performance Bluetooth Low Energy SoC. This SoC integrates all the essentials of a Bluetooth smart device which includes 32-bit 64MHz ARM Cortex-M0 with 512kB Flash memory, digital interface support and high performance 2.4GHz RF transceiver. A high efficiency DCDC converter is integrated to provide a complete ultra low power SoC solution for stand-alone applications such as IoT and Wearable devices.

1.2 Key Features

- Fully qualified Bluetooth Low Energy 4.2 device
- 2.8mA RX radio current, 4.8mA TX radio current
- Cortex M0 32-bit MCU with max. 64MHz clock rate, much more user-friendly than RSIC MCU!
- Ultra low power and excellent performance 2.4GHz transceiver with built-in balun for compact layout area and low BOM cost
- 8 channel 1MSPS 10-bit SAR ADC
- Highly integrated SoC with 512kB Flash and 32kB Data RAM, OTA supported
- 32MHz and 32.768kHz crystal oscillator circuit with on-chip loading capacitors, no external loading capacitors needed
- Built in buck DCDC converter
- Built in 64MHz and 32.768kHz RC oscillator
- Quadrature Decoder
- Native 7816 interface supported
- Infrared(IR) modulator and receiver supported
- Communication interface options
 - Master I2C x2
 - Master Three/Four-Wire SPI x2 (32MHz)
 - UART x2
- Digital peripherals
 - PWM x6
 - RTC
- Serial Wire Debug(SWD) supported

1.3 Applications

- Wearable device (wristband, smart watch, etc.)
- Smart home and industrial automation
- Remote controller
- Health applications (smart scale, etc.)
- HID device (smart remote controller, etc.)

1.4 Key Parameters

Parameter	Value
Max. TX Power	+4 dBm
RX Sensitivity	-94dBm
TX Current @0dBm*	4.8 mA
RX Current @-94dBm*	2.8 mA
Sleep Current w/ retention	2.7µA
Deep Sleep Mode Current	1 µA
Flash	512 kB
Data RAM	32 kB
Supply Voltage	1.8~3.6 V
GPIO	32/21 (QFN48/QFN32)
Operating Temperature, Tj	-40~+85 °C
Package Size –QFN32	5.0 x 5.0 x 1.0 mm
–QFN48	6.0 x 6.0 x 1.0 mm

*Condition: VDD=3V, DCDC enable.

For any additional inquiries, please contact us at:
<http://www.sydtek.com>

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2.0 Introduction

2.1 Overview

The SYD8811 chip is highly integrated with ARM® Cortex®-M0 processor, Radio Transceiver, Bluetooth Modem, Bluetooth Low Energy v4.2 baseband, Flash and SRAM, on-chip Balun and digital interfaces such as SPI/I2C/UART etc. The Cortex M0 can operate at 64MHz clock rate for heavy thread computing application, and can also operate at lower clock rate for simple data communication purpose. A built-in DCDC converter is integrated to provide full-solution SoC for stand-alone applications such as IoT and wearable devices.

Figure 1 shows the architecture block diagram of the chip. Refer to the subsequent chapters for detailed information on the functionality of the different interface blocks.

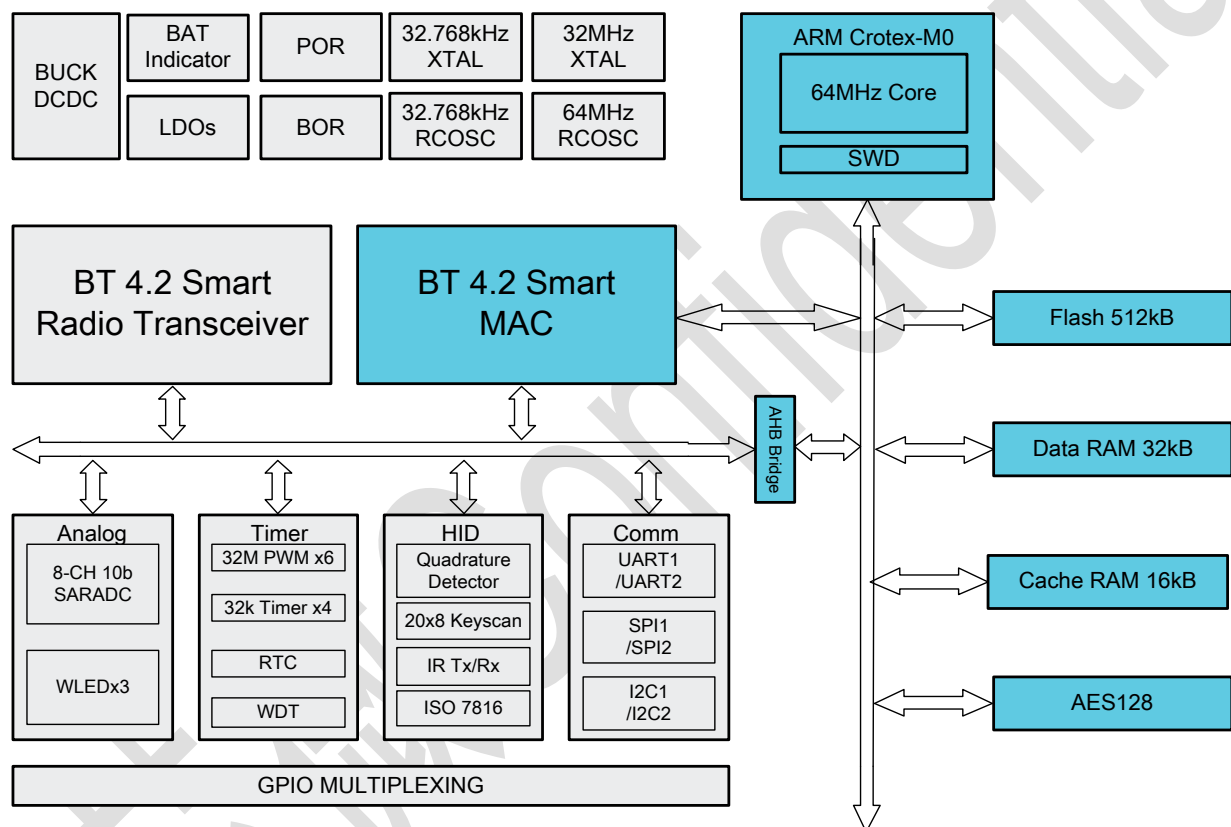


Figure 1. Functional Block Diagram

2.2 Terminology

Term	Description
GND	Ground
BiDir	Bi-Directional
PWM	Pulse Width Modulation
HID	Human Interface Device
GPIO	General Purpose Input / Output

2.3 Pin Assignment and Signal Description

2.3.1 QFN48 Pin Assignment and Signal Description

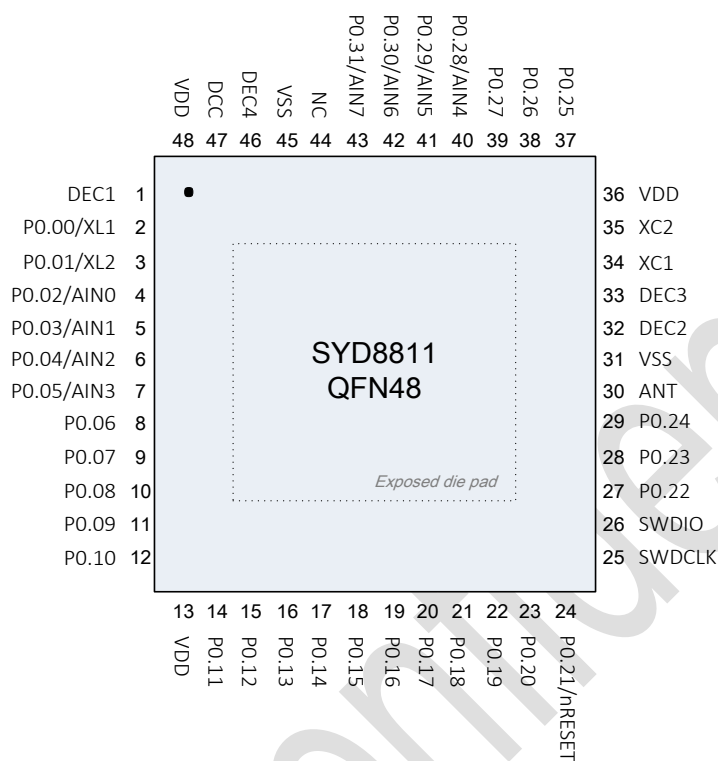


Figure 2. QFN48 pin assignments, top view (6mm*6mm)

Table 1. QFN48 pin assignments

Pin	Name	Type	Description
Left side of chip			
1	DEC1	Power	1.1V regulator digital supply decoupling
2	P0.00	Digital I/O	General purpose I/O
	XL1	Analog input	Connection for 32.768 kHz crystal (LFXO)
3	P0.01	Digital I/O	General purpose I/O
	XL2	Analog input	Connection for 32.768 kHz crystal (LFXO)
4	P0.02	Digital I/O	General purpose I/O
	AIN0	Analog input	SAADC input
5	P0.03	Digital I/O	General purpose I/O
	AIN1	Analog input	SAADC input
6	P0.04	Digital I/O	General purpose I/O

Pin	Name	Type	Description
7	AIN2	Analog input	SAADC input
	P0.05	Digital I/O	General purpose I/O
	AIN3	Analog input	SAADC input
8	P0.06	Digital I/O	General purpose I/O Capacitive touch
9	P0.07	Digital I/O	General purpose I/O Capacitive touch
10	P0.08	Digital I/O	General purpose I/O Capacitive touch
11	P0.09	Digital I/O	General purpose I/O Capacitive touch
12	P0.10	Digital I/O	General purpose I/O
Lower side of chip			
13	VDD	Power	Power supply
14	P0.11	Digital I/O	General purpose I/O
15	P0.12	Digital I/O	General purpose I/O
16	P0.13	Digital I/O	General purpose I/O
17	P0.14	Digital I/O	General purpose I/O
18	P0.15	Digital I/O	General purpose I/O
19	P0.16	Digital I/O	General purpose I/O
20	P0.17	Digital I/O	General purpose I/O
21	P0.18	Digital I/O	General purpose I/O
22	P0.19	Digital I/O	General purpose I/O
23	P0.20	Digital I/O	General purpose I/O
24	P0.21 nRESET	Digital I/O	General purpose I/O Configurable as pin reset
Right side of chip			
25	SWDCLK	Digital input	Serial wire debug clock input for debug and programming
26	SWDIO	Digital I/O	Serial wire debug I/O for debug and programming
27	P0.22	Digital I/O	General purpose I/O
28	P0.23	Digital I/O	General purpose I/O
29	P0.24	Digital I/O	General purpose I/O
30	ANT	RF	Single-ended radio antenna connection

Pin	Name	Type	Description
31	VSS	Power	Ground (radio supply)
32	DEC2	Power	1.1 V regulator supply decoupling
33	DEC3	Power	1.1 V regulator supply decoupling
34	XC1	Analog input	Connection for 32 MHz crystal
35	XC2	Analog input	Connection for 32 MHz crystal
36	VDD	Power	Power supply
Upper side of chip			
37	P0.25	Digital I/O	General purpose I/O
38	P0.26	Digital I/O	General purpose I/O
39	P0.27	Digital I/O	General purpose I/O
40	P0.28	Digital I/O	General purpose I/O
41	AIN4	Analog input	SAADC input
	P0.29	Digital I/O	General purpose I/O
42	AIN5	Analog input	SAADC input
	P0.30	Digital I/O	General purpose I/O
43	AIN6	Analog input	SAADC input
	P0.31	Digital I/O	General purpose I/O
44	AIN7	Analog input	SAADC input
	NC		No connect, Leave unconnected
45	VSS	Power	Ground
46	DEC4	Power	1.25V DCDC output voltage decoupling
47	DCC	Power	DC/DC regulator output
48	VDD	Power	Power supply
Bottom of chip			
Die pad	VSS	Power Ground pad	Exposed die pad must be connected to ground (VSS)

2.3.2 QFN32 Pin Assignment and Signal Description

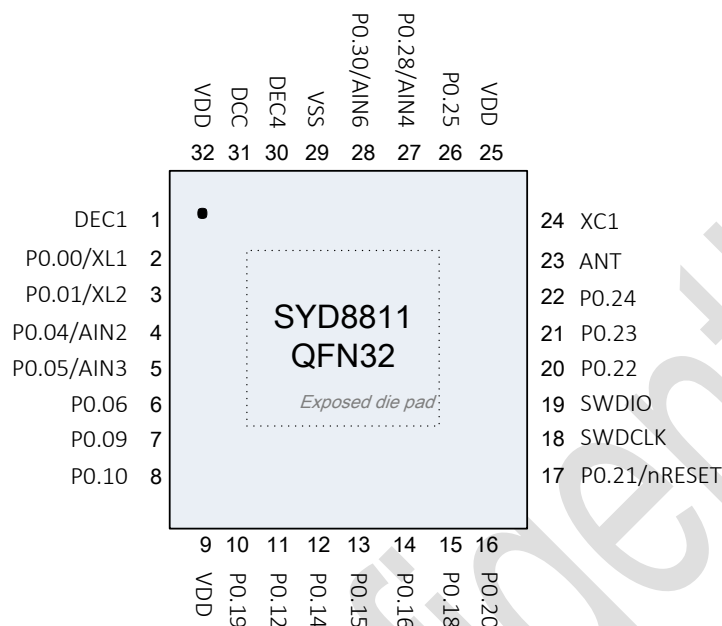


Figure 3. QFN32 pin assignments, top view (5mm*5mm)

Table 2. QFN32 pin assignments

Pin	Name	Type	Description
Left side of chip			
1	DEC1	Power	0.9 V regulator digital supply decoupling
2	P0.00	Digital I/O	General purpose I/O
	XL1	Analog input	Connection for 32.768 kHz crystal (LFXO)
3	P0.01	Digital I/O	General purpose I/O
	XL2	Analog input	Connection for 32.768 kHz crystal (LFXO)
4	P0.04	Digital I/O	General purpose I/O
	AIN2	Analog input	SAADC input
5	P0.05	Digital I/O	General purpose I/O
	AIN3	Analog input	SAADC input
6	P0.06	Digital I/O	General purpose I/O Capacitive touch
7	P0.09	Digital I/O	General purpose I/O
8	P0.10	Digital I/O	General purpose I/O

Pin	Name	Type	Description
Lower side of chip			
9	VDD	Power	Power supply
10	P0.19	Digital I/O	General purpose I/O
11	P0.12	Digital I/O	General purpose I/O
12	P0.14	Digital I/O	General purpose I/O
13	P0.15	Digital I/O	General purpose I/O
14	P0.16	Digital I/O	General purpose I/O
15	P0.18	Digital I/O	General purpose I/O
16	P0.20	Digital I/O	General purpose I/O
Right side of chip			
17	P0.21 nRESET	Digital I/O	General purpose I/O Configurable as pin reset
18	SWDCLK	Digital input	Serial wire debug clock input for debug and programming
19	SWDIO	Digital I/O	Serial wire debug I/O for debug and programming
20	P0.22	Digital I/O	General purpose I/O
21	P0.23	Digital I/O	General purpose I/O
22	P0.24	Digital I/O	General purpose I/O
23	ANT	RF	Single-ended radio antenna connection
24	XC1	Analog input	Connection for 32 MHz crystal
Upper side of chip			
25	VDD	Power	Power supply
26	P0.25	Digital I/O	General purpose I/O
27	P0.28 AIN4	Digital I/O Analog input	General purpose I/O Capacitive touch SAADC input
28	P0.30 AIN6	Digital I/O Analog input	General purpose I/O Capacitive touch SAADC input
29	VSS	Power	Ground
30	DEC4	Power	1.2 V regulator supply decoupling Input from DC/DC regulator Output from 1.2 V LDO
31	DCC	Power	DC/DC regulator output
32	VDD	Power	Power supply
Bottom of chip			

Pin	Name	Type	Description
Die pad	VSS	Power Ground pad	Exposed die pad must be connected to ground (VSS)

3.0 Operating Specifications

3.1 Absolute Maximum Ratings

Table 3. Absolute Maximum Ratings

Parameters	Symbol	Min.	Max.	Unit	Notes
VDD Voltage	V _{VDD}	-0.4	V _{VDD} +0.3	V	
I/O Voltage	V _{DDIO}	-0.4	V _{DDIO} +0.3	V	
Relative Humidity	RH	0	50	%	Non-condensing, Non-biased
ESD	ESD _{HBM}		2	kV	Class 2 on all pins, as per human body model. JESD22-A114E with 15 sec zap interval.

Notes:

1. At room temperature.
2. Maximum Ratings are those values beyond which damage to the device may occur.
3. Exposure to these conditions or conditions beyond those indicated may adversely affect device reliability.
4. Functional operation under absolute maximum-rated conditions is not implied and should be restricted to the Recommended Operating Conditions.

3.2 Recommended Operating Conditions

Table 4. Recommended Operating Conditions

Description	Symbol	Min.	Typ.	Max.	Unit	Notes
Ambient Temperature	T _A	-40	25	125	°C	
Operating Junction Temperature	T _J	-40	-	125	°C	
Power Supply Voltage for Buck DCDC converter	V _{VDD}	1.8	3.3	3.6	V	Buck DCDC Power input supply. Includes ripples
I/O Supply Voltage	V _{DD}	1.8	3.3	3.6	V	Includes ripples
Regulator Output Voltage	V _{DEC1}	0.9	1.1	1.2	V	Power for internal digital circuit
Serial Clock Frequency	SPI_CLK	-	-	32	MHz	
	I2C_SCL	-	400 ¹	1000 ²	KHz	

Note: SYDTEK does not guarantee the performance if the operating temperature is beyond the specified limit.

3.3 Thermal Specifications

Table 5. Thermal Specifications

Parameters	Symbol	Min.	Typ.	Max.	Unit	Notes
Storage Temperature	T _S	-40	-	125	°C	
Lead-free Solder Temperature	T _P	-	-	245	°C	Refer to Package Handling Information document

3.4 DC Characteristics

Table 6. DC Electrical Specifications

Parameters	Symbol	Min.	Typ.	Max.	Unit	Conditions
DCDC Converter Input Voltage	V_{VDD}	1.8	3.3	3.6	V	
DCDC Converter Output Voltage	V_{Buck_OUT}	1.1	1.25	-	V	
DCDC Converter Output Current	I_{Buck_Out}	-	-	40	mA	Max current w/i keep setting output voltage
DCDC Converter Output Ripple	R_{Buck}	-	30	-	mV	Max. Ripple on DCDC converter output (Peak to Peak)
Power Consumption²						
TX RF Current @Pout = 0dBm			4.8		mA	@ V_{VDD} = 3V with DCDC enable
RX RF Current @Sensitivity level			2.8		mA	@ V_{VDD} = 3V with DCDC enable
Supply Current @ Sleep	I_{SLEEP}	-	2.7	-	μ A	@ V_{VDD} = 3V with DCDC enable
Supply Current @ Deep sleep	I_{PD}	-	1	-	μ A	@ V_{VDD} = 3V with DCDC enable

Notes:

- Electrical Characteristics are defined under recommended operating conditions.
- All the parameters are tested under operating conditions: V_{VDD} = 3.0V, DCDC Buck enable mode at T_A = 25°C

3.5 AC and Timing Characteristics

3.5.1 Power-On Sequence

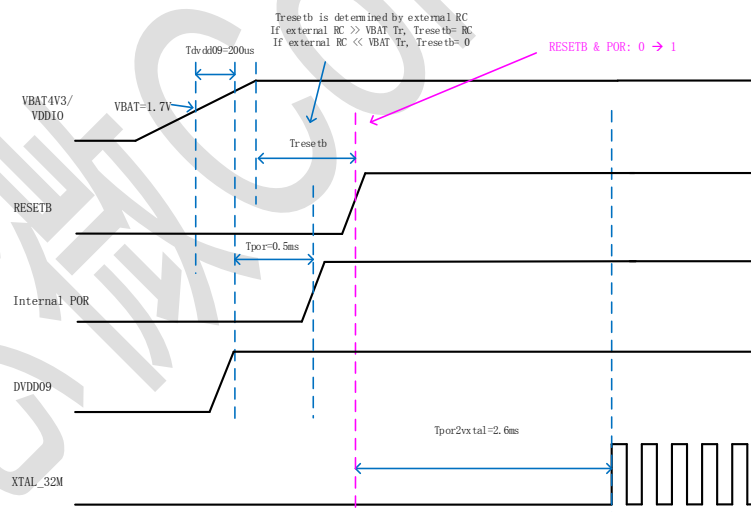


Figure 4. Power-On Sequence

3.5.2 32MHz Crystal Oscillator

The 32MHz Pierce crystal oscillator is designed for ultra low power consumption and high stability. The 32MHz oscillator can be trimmed without external capacitors. Two digital controlled trimming loading capacitors are integrated and optimally designed for 10pF XTAL. Digital controlled capacitors could ease and speed up tuning procedure of XTAL frequency accuracy. The simplified schematic of the 32MHz crystal is shown in Figure 5.

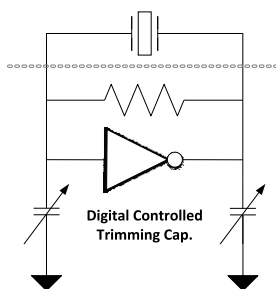


Figure 5. 32MHz Crystal Oscillator Circuit

Table 7. 32MHz Crystal Oscillator Specifications

Parameters	Symbol	Min.	Typ.	Max.	Unit	Conditions
Crystal Oscillator Frequency	F_{X32M}	-	32		MHz	
Crystal Oscillator Frequency tolerance	F_{X32M_TOL}	-	± 10	± 20	ppm	Frequency tolerance depends on XTAL Spec.
Equivalent series Resistor	ESR_{X32M}		30	100	Ω	
Loading Capacitor	C_{L_X32M}		10		pF	Built in digital controlled trimming loading cap, no external cap needed.
XTAL Drive Power	P_{DRIVE_X32M}			100	μW	
XTAL OSC Start Up Time	T_{START_X32M}		1.5	2.5	ms	Depends on XTAL

Notes: Electrical Characteristics are defined under recommended operating conditions

3.5.3 32.768kHz Crystal Oscillator

The 32.768 kHz oscillator is designed optimally for XTAL with C-Load =12.5pF , and no internal trimming capabilities and 32.768kHz clock is used as the clock source in the Sleep or Power Down modes.

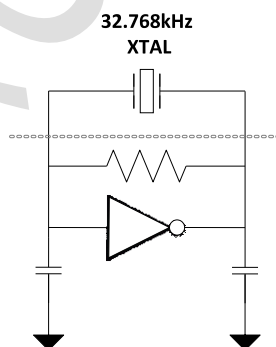


Figure 6. 32.768kHz Crystal Oscillator Circuit

Table 8. 32.768kHz Crystal Oscillator Specifications

Parameters	Symbol	Min.	Typ.	Max.	Unit	Conditions
Crystal Oscillator Frequency	F_{X32k}		32.768		kHz	
Crystal Oscillator Frequency tolerance	F_{X32k_TOL}		± 20		ppm	Frequency tolerance depends on XTAL Spec.
Equivalent series Resistor	ESR_{X32k}		50	80	$k\Omega$	

Load Capacitor	C_{L_X32k}	12.5		pF	Built internal fixed load cap for 12.5pF XTAL
XTAL Drive Power	P_{DRIVE_X32k}		1	uW	
XTAL Start Up Time	T_{START_X32k}	0.3	1	s	

3.5.4 64MHz RC Oscillator

The 64MHz RC oscillator is designed for high speed wake up and high computing power application. Due to characteristic of RC oscillator, calibration is needed before switching to 64MHz RC oscillator mode.

Table 9. 64MHz RC Oscillator Specifications

Parameters	Symbol	Min.	Typ.	Max.	Unit	Conditions
RC Oscillator Frequency	F_{RC64M}		64		MHz	
RC Oscillator Frequency tolerance	F_{RC64M_TOL}		± 1	± 5	%	
Oscillator Start Up Time	T_{ST_RC64M}		2.5		us	

Notes: Electrical Characteristics are defined under recommended operating conditions

3.5.5 32.768kHz RC Oscillator

The 32.768kHz RC oscillator is designed for low cost applications without additional 32.768kHz XTAL. Due to characteristic of RC oscillator, calibration is needed before switching to 32.768kHz RC oscillator mode.

Table 10. 32.768kHz RC Oscillator Specifications

Parameters	Symbol	Min.	Typ.	Max.	Unit	Conditions
RC Oscillator Frequency	F_{RC32k}		32.768		kHz	
RC Oscillator Frequency tolerance	F_{RC32k_TOL}		± 2		%	
RC Oscillator Frequency tolerance, Calibrated	F_{RC32k_TOL}		± 250	± 500	ppm	Calibration needed before switching to RC oscillator mode
Start Up Time	T_{START_X32K}		100		us	

Notes: Electrical Characteristics are defined under recommended operating conditions

3.6 RF Specifications

3.6.1 Transmitter RF Specification

Table 11. Transmitter Specifications

Parameters	Symbol	Min.	Typ.	Max.	Unit	Conditions
Frequency Range	FR_{TX}	2402	-	2480	MHz	
Max. Output Power	P_{O_MAX}	-		4	dBm	
Default Output Power	P_{O_DEF}		0		dBm	
Output Power Adjust Range	P_{O_ADJ}	-30		4	dBm	
Output Power Variation	P_{O_VAR}		2.0		dBm	All channels TX power variation
TX 20dB Bandwidth	BW_{20dB}			1150	kHz	
1 st Adjacent Channel Power	P_{AIC1}			-20	dBc	
2 nd Adjacent Channel Power	P_{AIC2}			-40	dBc	
Delta F1 Frequency Deviation	Δf_{1AVG}	225		275	kHz	
Delta F2 Frequency Deviation	Δf_{2AVG}	185			kHz	
AVG Delta F2/ Delta F1	Δf_{AVG}	0.8				$\Delta f_{2AVG}/\Delta f_{1AVG}$
Frequency Offset	F_{OFFSET}	-150		150	kHz	
Carrier Frequency Drift	CF_{DRIFT}			50	kHz	
Carrier Frequency Drift rate	CF_{DRIFT_Rate}			20	kHz/50 μ s	

2 nd Harmonics Power Level	Har _{2nd}	-40	dBm	@Pout = 0dBm
3 rd Harmonics Power Level	Har _{3rd}	-45	dBm	@Pout = 0dBm

Notes: Electrical Characteristics are measured under BLE specification and recommended operating conditions

3.6.2 Receiver RF Specification

Table 12. Receiver Specifications

Parameters	Symbol	Min.	Typ.	Max.	Unit	Conditions
Frequency Range	FR _{RX}	2402		2480	MHz	
Maximum Input Power	RX _{MAX}		0		dBm	
Ideal Signal Sensitivity	SEN _{IDEAL}		-94		dBm	
Dirty Signal Sensitivity	SEN _{DIRTY}		-92		dBm	
C/I and Selectivity						
C/I Co-Channel	C/I _{CO}		9		dB	
C/I Adjacent +1MHz	C/I _{1M}		-1		dB	
C/I Adjacent +2MHz	C/I _{2M}		-38		dB	
C/I Adjacent \geq +3MHz	C/I _{3M}		-48		dB	
C/I Image Channel	C/I _{IMG}		-25		dB	
C/I Image+1M Channel	C/I _{IMG+1M}		-35		dB	
Inter-Modulation Performance						
IMD performance	IMD		-24		dBm	3rd, 4th and 5th offset channel
Blocking Performance						
Blocking 30~2000MHz	P _{BLK_30~2000} MHz	-10			dBm	
Blocking 2003~2399MHz	P _{BLK_2003~23} 99MHz	-30			dBm	
Blocking 2484~2997MHz	P _{BLK_2484~29} 97MHz	-30			dBm	
Blocking 3000MHz~12.75GHz	P _{BLK_3~12.75G} Hz	-10			dBm	

Notes: Electrical Characteristics are measured under BLE specification and recommended operating conditions

4.0 Design References

4.1 Application Schematics

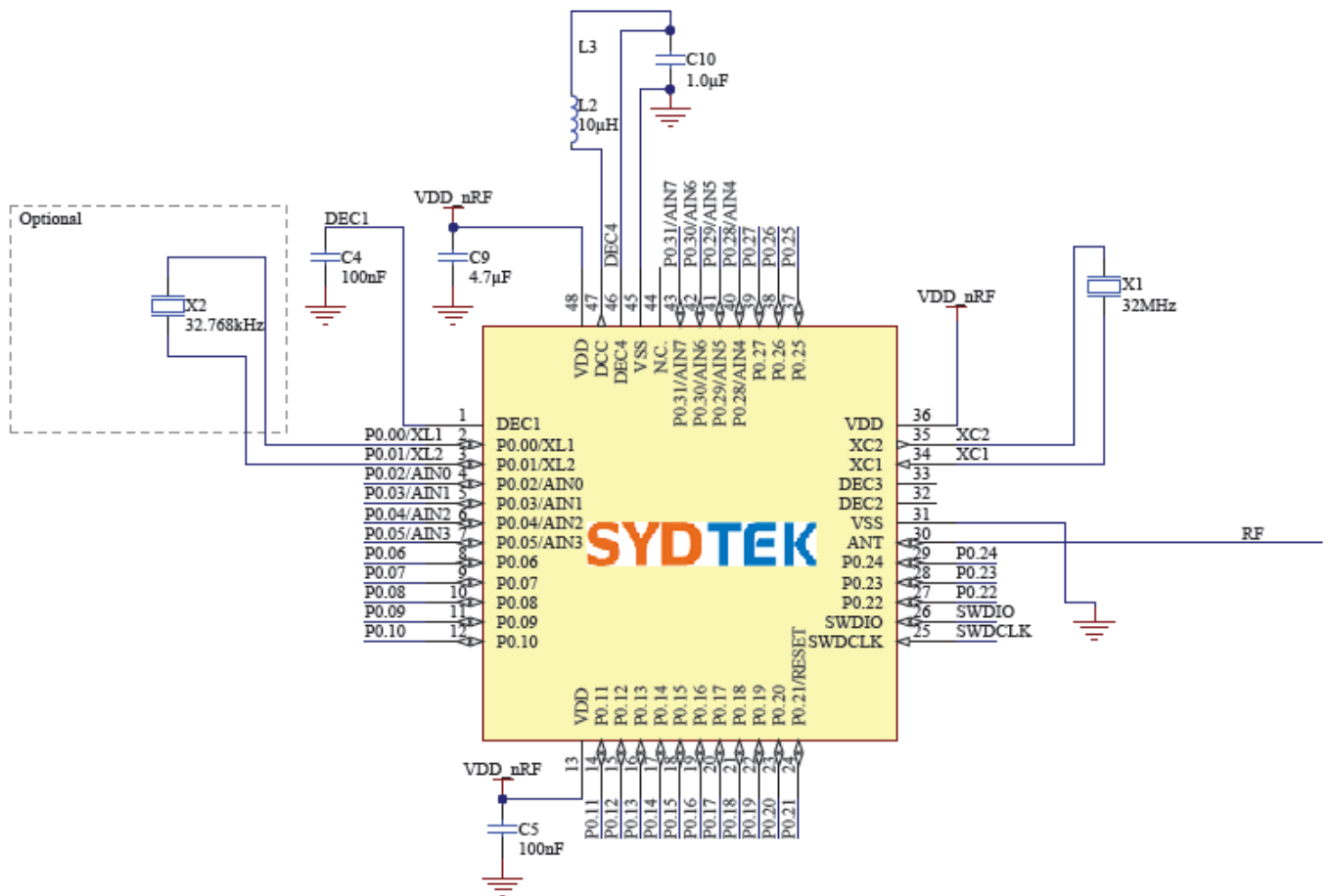


Figure 7. Reference Application Circuit (32.768k xtal is optional)

Table 13. BOM of SYD8811

Designator	Value	Description	Footprint
C4, C5	100 nF	Capacitor, X5R, $\pm 20\%$	0402
C9	4.7 μ F	Capacitor, X5R, $\pm 20\%$	0603 or 0402
C10	10 μ F recommended	Capacitor, X5R, $\pm 20\%$	0603
L2	4.7 μ H	Inductor, IDC, min = 30 mA, $\pm 20\%$	0603
U1	SYD8811	ULP Bluetooth low energy SoC	QFN48
X1	32 MHz	32 MHz, CL = 10 pF, Tol: ± 10 ppm	3225
X2 (optional)	32.768 kHz	32.768 kHz, CL = 12.5 pF, Tol: ± 20 ppm	3215

4.2 Layout Design Guidelines

Precaution: PCB layout is extremely important to minimize parasitical capacitance and line inductance.

The following layout guidelines are recommended to achieve optimum performance.

1. Make sure RF 50-ohm trace is with GND continuation.
2. Place the DCDC inductor close to the DCC pin. Keep the traces short and wide enough.
3. Place bypass capacitors near the input/output pins.
4. Place 4.7uF C9 near Pin48 VDD.
5. Route PIN45 VSS to gnd plane by VIA (4layer PCB) , or route PIN45 VSS to bottom layer by VIA (2layer PCB), DO NOT connect PIN45 VSS to top layer gnd; ** PIN45 VSS is dirty DCDC gnd.
6. Connect PIN49 GND to top layer GND though the three corners (except PIN45 VSS corner), and connect to bottom layer GND by 9 VIAs;
7. Place the crystal and its components close to the oscillator side and near the oscillator pins.
8. Ensure that the ground plane under the oscillator and its components are in good quality.
9. Avoid long connections to the crystal and also to the load capacitor which may create a large loop on the PCB.
10. Do not route any digital-signal lines on the opposite side of the PCB under the RF trace and crystal area.
11. Keep other digital signal lines, especially clock lines and frequently switching signal lines, as far away from crystal/analog/RF connections as possible.
12. Place at least 9 ground vias directly under IC thermal PAD for good grounding and thermal dissipation.

5.0 Mechanical Specifications

5.1 Mechanical Dimension

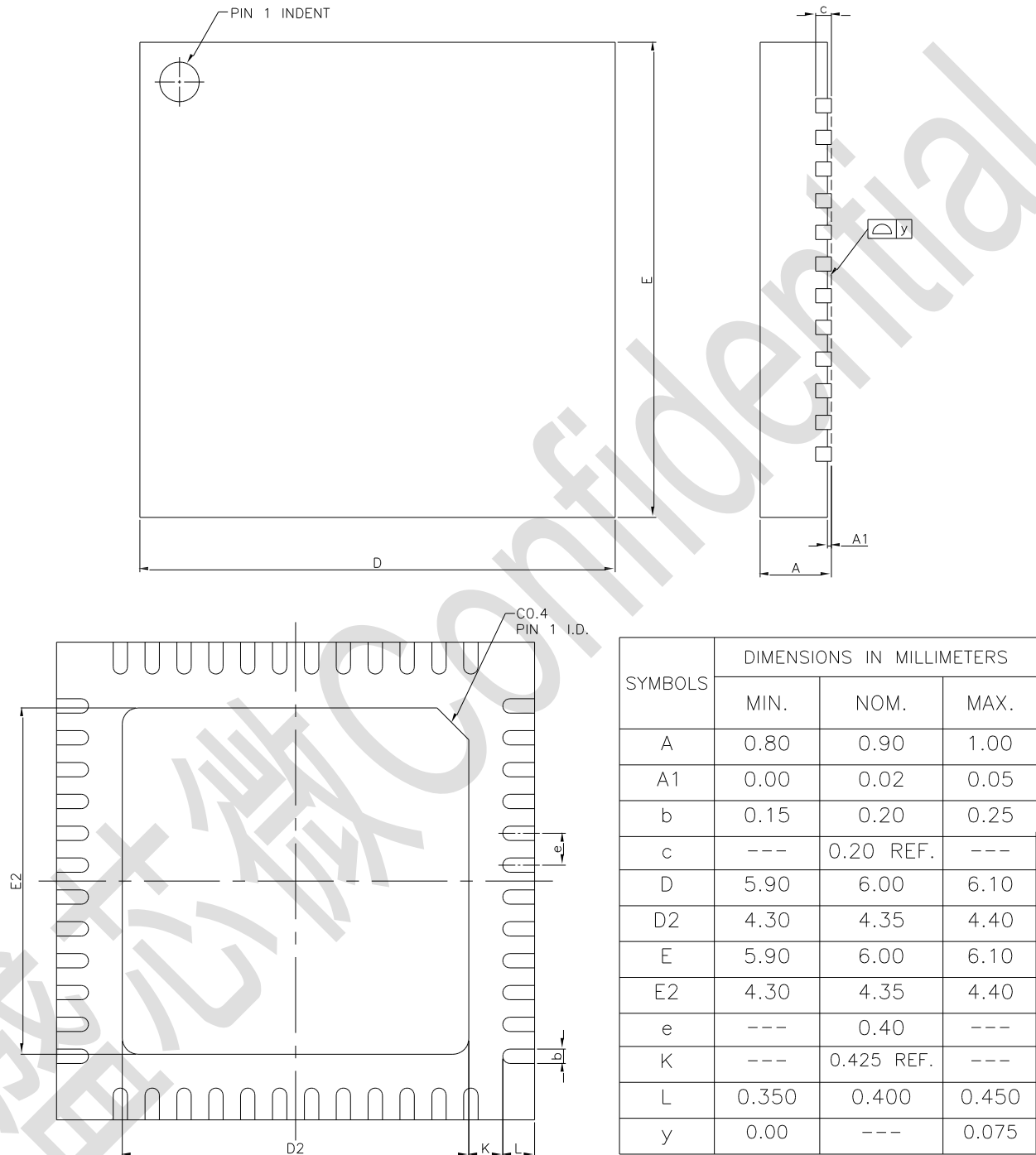


Figure 8. Package Outline Diagram and Dimension

5.2 Package Marking

Refer to Figure 9 for the code marking location on the device package.



Figure 9. Package Marking (QFN48: 6*6, QFN32 5*5)

Table 14. Code Identification

Marking	Description
LYWWXXXXXXXX	SYDTEK Date Code
	Y: Assembly year
	e.g. (Yearly 2018) -> 8
	WW: Assembly week
	e.g. (Weekly 16) -> 16
	XXXX: NO.
	e.g. 433CE12

6.0 Power States & Sequence

6.1 Operation Mode

State	Functional Description
Deep sleep	All power supplies are off except I/O for pin wake-up. All clocks are gated. System can be woken up by configured external pin. When it happens, SYD8811 resets from boot-up state.
Sleep	Active clocks (32MHz xtal and 64MHz RCOSC) are off, and the sleep clock (32.768kHz) remain working. Certain engines' power are off. Two types of sleep modes are provided in SYD8811. When CPU uses 32MHz crystal clock together with Bluetooth, it follows Bluetooth sleep mode aligning to connection interval. When CPU uses internal 64MHz RC clock, it can set CPU sleep mode independently and woken up by timer or Bluetooth interrupts.
Standby	This is the default state after power-up. All clocks are working but the RF is inactive.
TX	This mode is entered when Bluetooth link-layer determines to send transmission packets.
RX	This mode is entered when Bluetooth link-layer determines to receive an incoming packet.

7.0 System Description

7.1 ARM Cortex M0

The ARM® Cortex®-M0 processor is the smallest ARM processor available. It provides ultra low power consumption and minimal code of the processor to enable developers to achieve 32-bit performance. With its friendly architecture, users can develop applications easily and fast.

SYD8811 supports dynamic clock technology for various applications ranging from 8MHz to 64MHz. The CPU clock can be configured to use internal 64MHz RC clock or 32MHz crystal clock. When using RC clock, MCU can run independently with Bluetooth link-layer and switch on and off at users' discretion. When using 32MHz crystal clock, it should follow the working period of Bluetooth (the Bluetooth working period can be determined by MCU).

SWD (Serial-Wire Debug) is supported for powerful debug and trace features with two connection pins.

SYD8811 has 24kB ROM for boot-up and BLE protocol stack, 512kB flash for profile/application, 32kB exchange/data SRAM.

7.2 Memory

- ROM: 32kB internal ROM is for the Boot code and Bluetooth Low Energy protocol stack firmware.
- Data RAM: 32kB Data RAM is integrated, 12kB will be used up by ROM(BLE stack), 20kB is available for application.
 - 0x2000 0000 ~ 0x2000 0C00 (3kB) is used by ROM.
 - 0x2000 0C00 ~ 0x2000 8000 (29kB) is available for application
- Flash: 512kB flash is integrated for code and firmware storage.

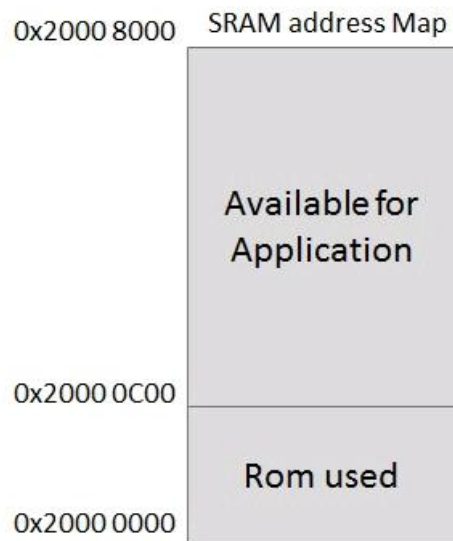


图 10. Data RAM 地址映射

7.3 Bluetooth Low Energy Core

The Bluetooth Low Energy Core is SIG Qualified. It is fully compliant with Bluetooth Smart v4.2 slave-role controller and provides qualified features as below:

- Bluetooth low energy stack: All layers up to GATT including (PHY, LL, HCI, L2CAP, GAP, SM, ATT/GATT)
- Slave-Role Link layer
 - Slave-required PDU types
 - Encryption/Decryption
- L2CAP

- Slave connection update
- Attribute channel
- Security channel
- GAP/ATT/GATT: Mandatory protocols
- Security Management
 - Key generation and passing
 - Automatic security engine
- DTM: For RF qualification
- Profile configuration
 - Initialization
 - Flexibility and testability

7.4 Radio Transceiver

The SYD8811 integrates high performance 2.4GHz radio transceiver for Bluetooth radio specification. With the built-in on-chip balun, SYD8811 does not need external balun circuit to minimize BOM. The integrated high efficiency PA can transmit up to +4dBm RF power for class 2 operation, while the integrated low-IF receiver can provide excellent sensitivity up to -94dBm and outstanding interference rejection capability.

7.5 General Purpose ADC (SAADC)

The SYD8811 integrates a low power 10-bit general purpose Analog-to-Digital Converter (GPADC) with 1MHz sampling rate. It can operate as a 9-channel ADC by switching the GPADC input. One channel is for internal Battery Voltage detection (V_{VDD}), while the other eight are configured to monitor eight GPIOs. For better accuracy, internal reference voltage calibration is preferred. Sensing applications as battery monitoring, temperature resister, analog signal sampling could be applied with this GPADC.

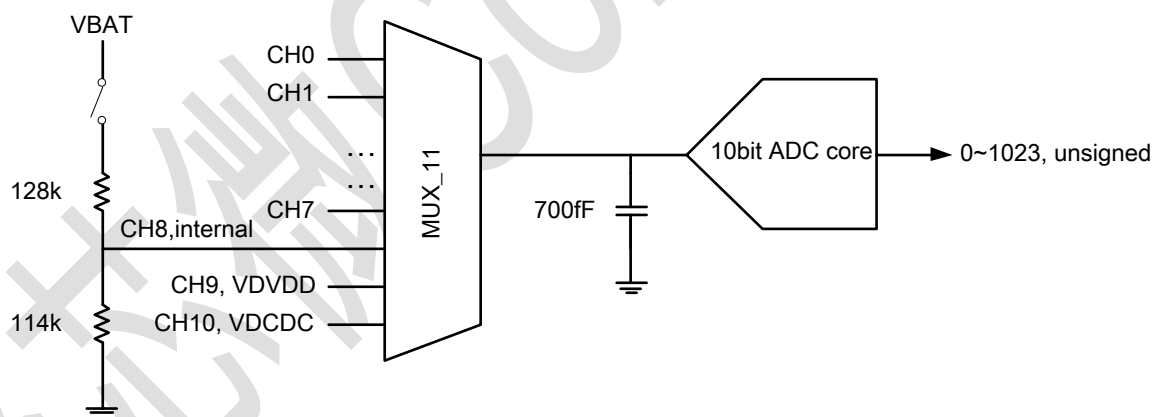


Figure 11. GPADC Internal Channel MUX and Resister Divider Configuration

7.6 Power Management

The SYD8811 integrates a power management unit for handheld or wearable devices with DCDC converter. The DCDC converter transforms battery voltage to a lower/higher internal voltage with minimal power loss. The DCDC converter could provide excellent power efficiency with adaptive loading current setting. The DCDC Buck converter can be bypassed when the supply voltage drops to the lower limit of the voltage range, and external DCDC converter is also supported. It can provide power solution for one-cell Lithium-Ion, one-cell or two serial alkaline battery applications where the output voltage is adjustable, 1.15V~3.6V.

7.6.1 Buck Converter

Higher performance DCDC Buck converter would bring up better battery life time. To ensure longest battery life, Buck converter has an optional bypass mode under light load current. The reduction in supply voltage level from a high voltage to a low voltage reduces the peak power drain from the battery. For better conversion efficiency, DC resistance (R_{DC}) should be less than 0.25ohm.

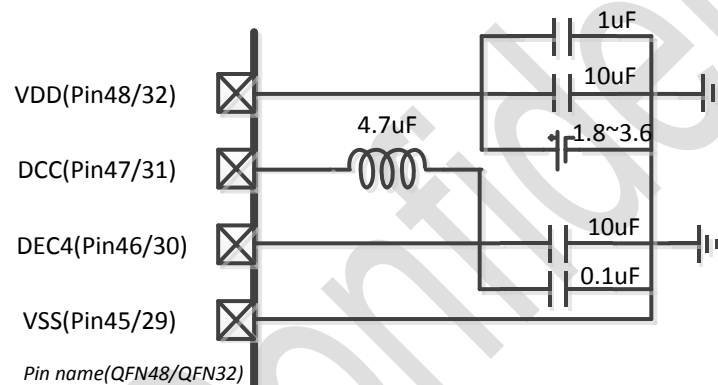


Figure 12. DCDC Buck Converter Configuration

Table 15. Buck Converter Specifications

Parameters	Symbol	Min.	Typ.	Max.	Unit	Conditions
Input Voltage	$V_{In,Buck}$	1.8	3.3	3.6	V	
Output Voltage	$V_{DCDC,Buck}$	1.8	3.3	3.6	V	
Converting Efficiency	Eff_{Buck}		88		%	@10mA Loading current
Maximum Load Current	$I_{Load,Buck}$			40	mA	
Output Ripple Voltage	$V_{RIPPLE,Buck}$		30		mV	

7.7 GPIO

SYD8811 offer 32 GPIOs and 2 SWD debug ports (SWDCLK, SWDIO). SWDCLK and SWDIO pins should be make sure that keep Low during SYD8811 booting procedure. The each GPIO supports easy configuration mode, that is, the selected function could be set on each GPIO.

GPIO has the following user-configurable features:

- Up to 32 GPIO pins per GPIO port
- Configurable output drive strength
- Internal pull-up resistors
- Input polarity free selection
- Wake-up from high or low level triggers on all pins
- Trigger interrupt on state changes on any pin
- All pins can be individually mapped to interface blocks for layout flexibility
- Hardware Debounced for application

7.8 Timer

SYD8811 integrates 4 low speed Timers and 1 high speed Timer.

7.8.1 Low Speed Timer

SYD8811 provide 4 low speed timers with 32-bit width.

Timer0~Timer3 are running with 32.768kHz clock from XTAL or LPO.

Timer interrupt can wakeup CPU from sleep mode. Timer3 is reserved for Rom Code.

7.8.2 High Speed Timer

The high speed timer works with the 32MHz RC clock, which has 16-bit width for high speed and accurate timing application. Two operating modes are provided, one -time or continuous, an interrupt to MCU can be triggered by timer at the end of period.

7.9 Real Time Clock (RTC)

SYD8811 offer one RTC timer for real time clock application.

7.10 Watch Dog Timer (WDT)

SYD8811 offer one 16-bit countdown watchdog timer for supervisor purpose. It also runs at 32.768kHz clock for maximum 2sec supervisor time to execute system reset due to a hardware fault or program error.

7.11 SW Encryption

SYD8811 offer 48bits encryption key for flash code protection.

7.12 AES Encryption Engine

The AES engine accelerates the algorithm calculations that are needed for implementing the user defined security algorithm. The AES encryption block supports 128 bit AES encryption. It can be used for a range of cryptographic functions like hash generation, digital signatures, and keystream generation for data encryption/decryption.

8.0 Peripheral

8.1 Hardware Keyscan

SYD8811 provides an 8x20 keyscan decoder for maximum 8 rows and 20 columns. The row and column could be assigned in specified IO for flexible configuration and layout.

When key is pressed, the keyscan circuit would auto scan the defined matrix and report to firmware in FIFOs.

8.2 Quadrature Decoder

SYD8811 provides a quadrature decoder for HID application. It could detect quadrature encoder signals and report to firmware in FIFOs. Also support can sleep wakeup function.

8.3 CapDetection

SYD8811 integrates one self-capacitance system, CapDetection, by counting charging clock. It is easy for comparing the capacitance difference on touch sensors. When a finger is placed on the touch sensor, CapDetection would estimate more capacitance on this sensor. CapDetection is simple and suited for single-touch sensors, such as buttons and sliders application.

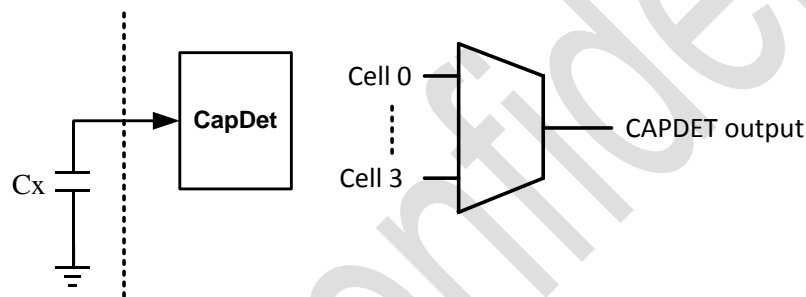


Figure 13. CapDetection Mux Configuration

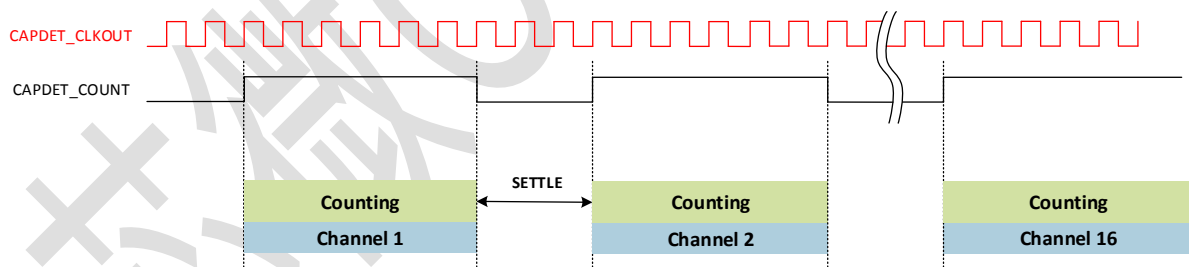


Figure 14. CapDetection scan timing

8.4 PWM

SYD8811 integrates four channel low speed PWM and six channel high speed PWM.

8.4.1 High speed PWM

SYD8811 integrates six channels high speed PWM with max. 32MHz clock with the following characters

- The period can be configured (four channels are the same).
- Each channel can be configured its ratio and initial polarity independently.
- The period, duty cycle can be update dynamically (be in effect next period)
- The pulse could to be center-aligned or edge-aligned.

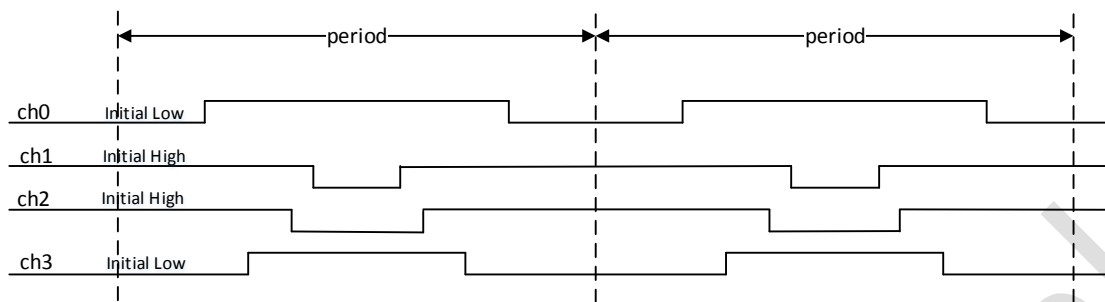


Figure 15. Center-aligned PWM

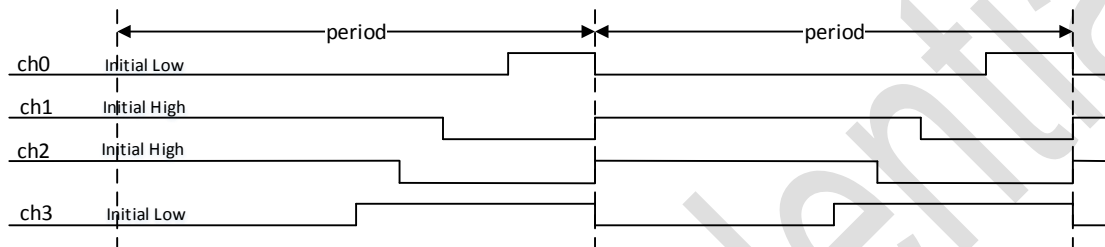


Figure 16. Edge-aligned PWM

8.4.2 Low speed PWM (LED Controller)

SYD8811 integrates four adjustable PWM generators which are controlled by individual register and could be mux out at three different GPIOs. The minimum positive or negative width of PWM is 1/32ms and flexible setting ranges from 1 to 255 steps. Buzzer or LED dimming could be controlled by PWM signal with pre-defined PWM duty.

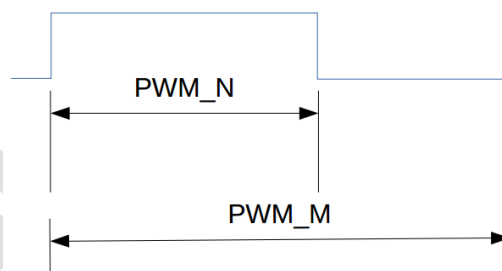


Figure 17. PWM Timing Setting Diagram

SYD8811 integrate LED controller which provide general On-OFF mode and Breathing light mode. The minimum LED on width is 1/32s with max 255 steps. LED ON-OFF repetition times could be configured as continuous or 1~127 times. Register table has setting description details. T1, T2, T3 are 8-bit width control register with minimum step 31.25ms.

For Breathing light mode, min, max, T4 are 8-bit width control register with minimum step 0.5ms. The sp is defined as breath mode speed with 4-bit width control register with minimum step, 31.25us.

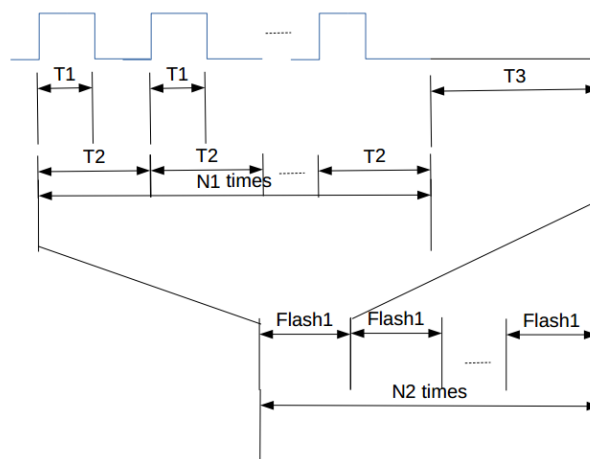


Figure 18. LED ON-OFF Setting Diagram

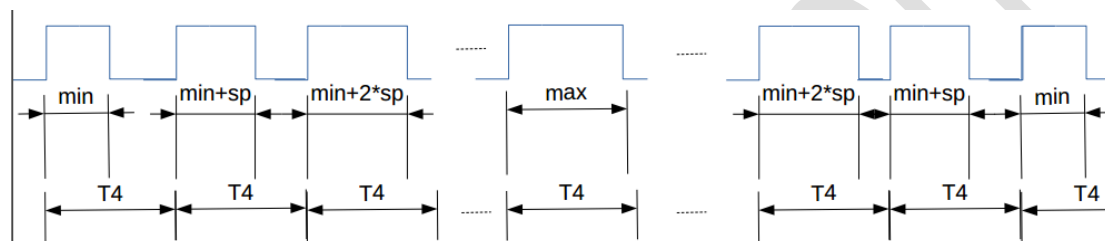


Figure 19. LED Breathing Light Setting Diagram

9.0 Interfaces

9.1 UART

The SYD8811 has two sets of UART interface (UART0, UART1) for serial asynchronous communication between devices. UART-0 has CTS/RTS hard flow control for option. Data frame configuration is as eight (8) data bits, with parity bit, and one (1) stop bit shown figure below.



Figure 20. UART Data Frame

Table 16. UART Characteristics

Parameters	Symbol	Min.	Typ.	Max.	Unit	Conditions
Baud Rate	BR	1200		921600	bps	
Baud Rate Accuracy	BR _{ACCU}			3.0	%	

9.2 I2C

The SYD8811 has two sets of I2C interface (I2C_0, I2C_1) for 2-wire bi-directional communication between devices. The I2C supports wide range of data rate from 31.25kHz to 1000kHz in register controls. Multiple Read modes are supported as current read, random read, and sequential read. Write mode also support byte write and page write.

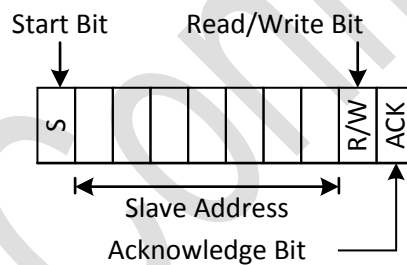


Figure 21. I2C Control Byte Format

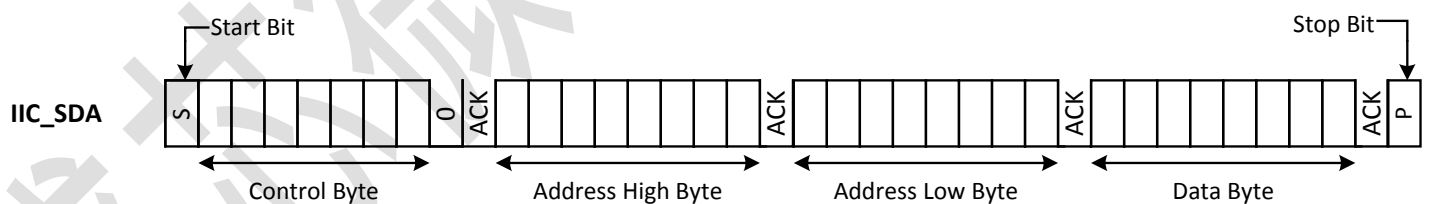


Figure 22. I2C Byte Write Format

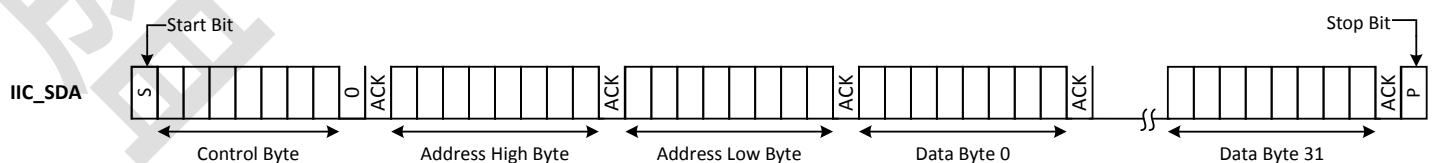


Figure 23. I2C Page Write Format

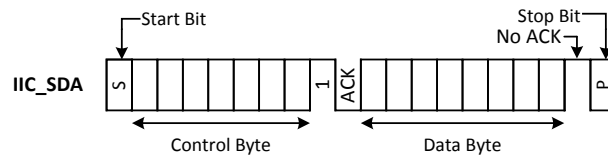


Figure 24. I2C Current Read Format

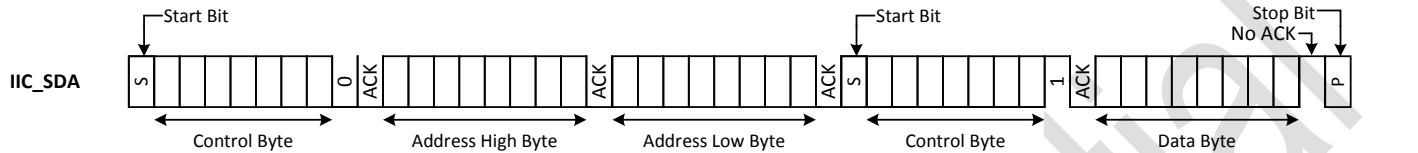


Figure 25. I2C Random Read Format

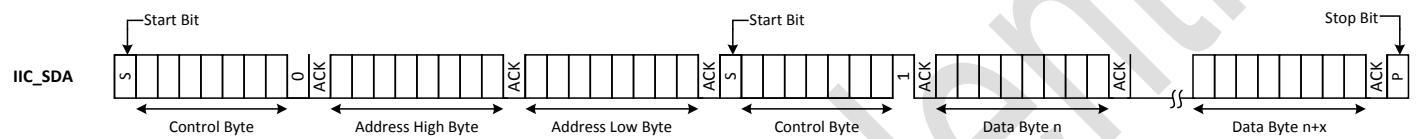


Figure 26. I2C Sequential Read Format

9.3 SPI

The SYD8811 provides two configurations of SPI interfaces. One is four wire SPI, as CSN (chip select), SCLK (clock), SDI (MOSI data) and SDO (MISO data) and the other is two or three wire SPI interface as CSN (chip select) – optional, SCLK (clock), SDIO (bi-directional Data). These two configurations are for master operation only, slave mode is not supported.

9.3.1 Packet Formats

The transmission protocol consists of the two operation modes:

- Write Operation.
- Read Operation.

Both of the two operation modes consist of two bytes. The first byte contains the address (seven bits) and has bit-7 as its MSB to indicate data direction. The second byte contains the data.

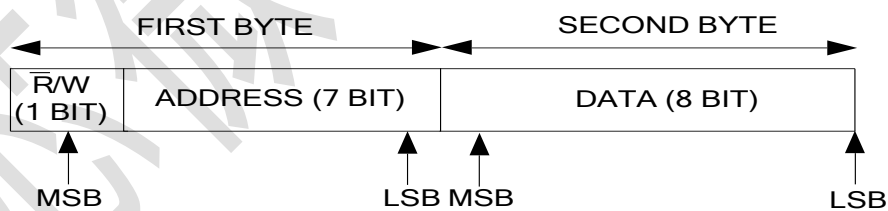


Figure 27. Four-wire or Three/Two-wire SPI Transmission Protocol

9.3.2 Write Operation

A write operation is always initiated by the SYD8811 and consists of two bytes, which the data is going from the host controller to the device. The first byte contains the 7 bits address and has a "1" as its MSB to indicate data direction. The second byte contains the full 8 bits data. The communication is synchronized by SCLK. The SYD8811 changes SDIO or SDI on the falling edges of SCLK and the device reads SDIO or SDI on the rising edges of SCLK.

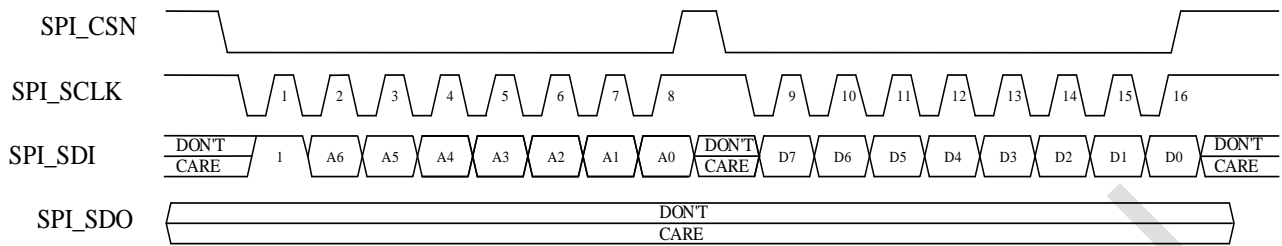


Figure 28. Four-wire SPI Write Operation

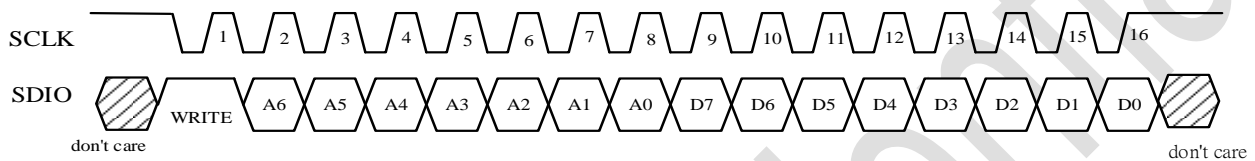


Figure 29. Three/Two-wire SPI Write Operation

9.3.3 Read Operation

A read operation is initiated by the host controller and consists of two bytes. The first byte contains 7-bit address specified by SYD8811 and has a "0" as its MSB to indicate data direction. The second byte contains the full 8 bits data and is driven by the slave device. This communication is synchronized by **SPI_SCLK**. For three/two-wire SPI, **SDIO** is changed on the falling edges of **SCLK** and is read on every rising edge of **SCLK**. SYD8811 release **SDIO** bus and handover the control of **SDIO** bus to the device on the falling edge of last address bit.

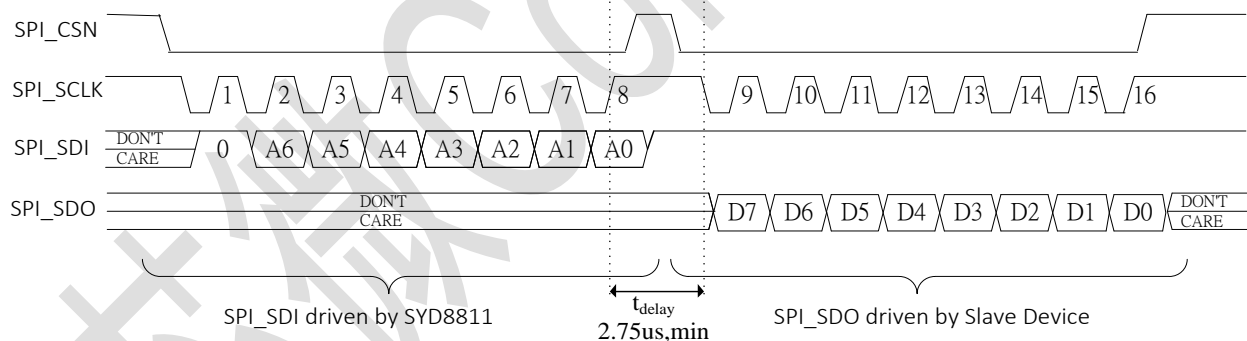


Figure 30. Four-wire SPI Read Operation

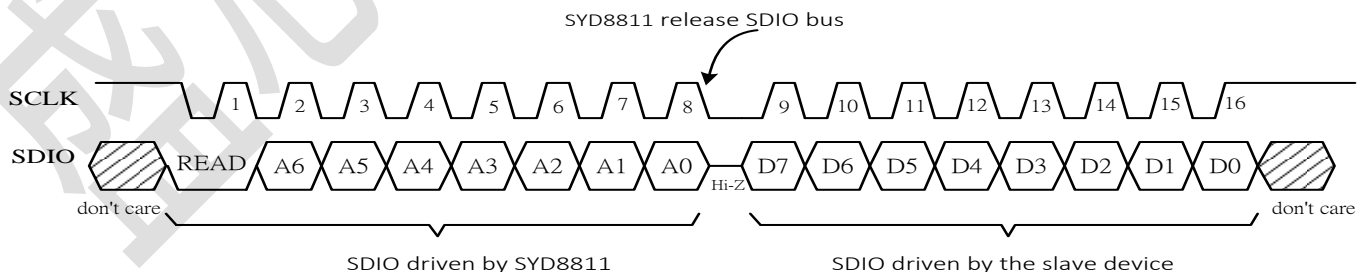


Figure 31. Three/Two-wire SPI Read Operation

9.4 ISO-7816-3

SYD8811 integrates one Smart Card Controller supports asynchronous 3V smartcards. The device is controlled by an ISO 7816-3 interface and is capable of card activation 、 deactivation 、 cold/warm reset 、 ATR parsing and data exchange.

- Compliant to ISO/IEC 7816-3: 1997
- Supports FIFO 8 bytes
- Interrupt report
- Flexible clock frequency and baud rate
- Parity/error check and resend
- T=0 protocol
- Wait time configuration
 - ATR wait time
 - Reset time
 - Guard time

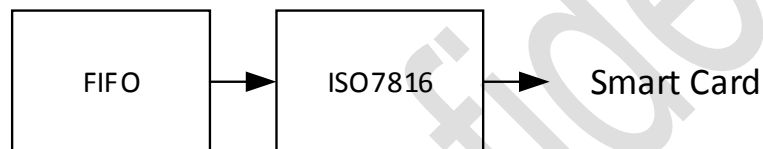


Figure 32. Function block of ISO7816

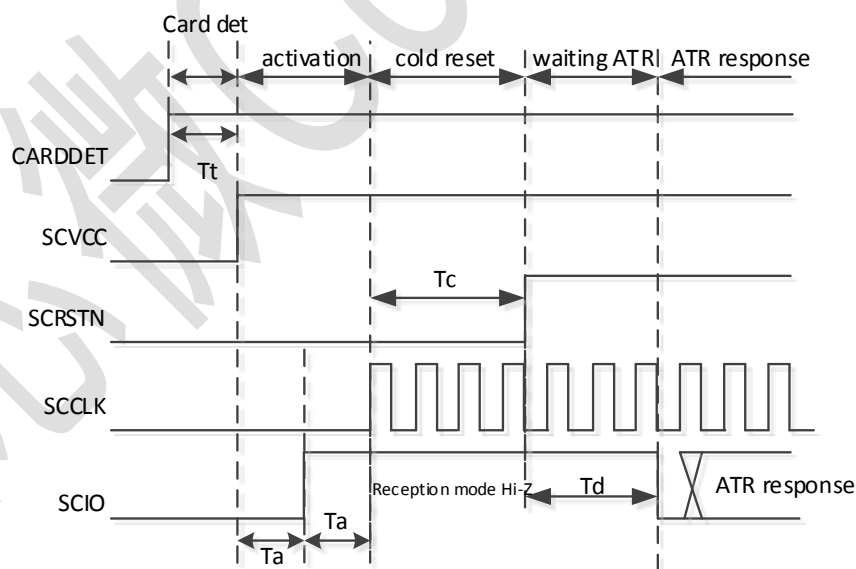


Figure 33. Activation, Cold Reset and ATR

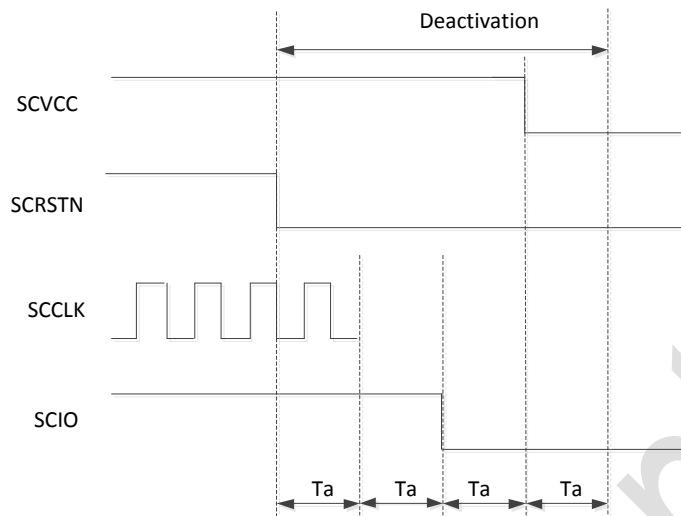


Figure 34. Deactivation Sequence

9.5 IR Transmitter and Receiver

SYD8811 integrates an IR transmitter and Receiver for remote controller applications.

9.5.1 IR Transmitter

The Infrared generator provides a flexible way of transmitting any IR code used in remote controls. It has an efficient message queue where users can describe the waveform of a specific IR command in just a few bytes independently from the protocol.

- Flexible carrier frequency and duty cycle.
- Flexible MARK and SPACE.
- Any IR remote control protocol.
- Supported 8 commands message queue in the FIFO.
- Interrupt report

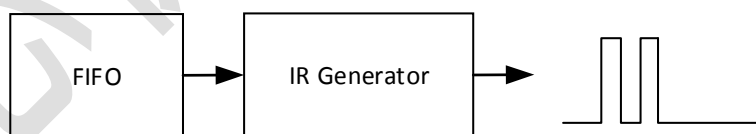


Figure 35. Function block of IR Generator

NEC code:

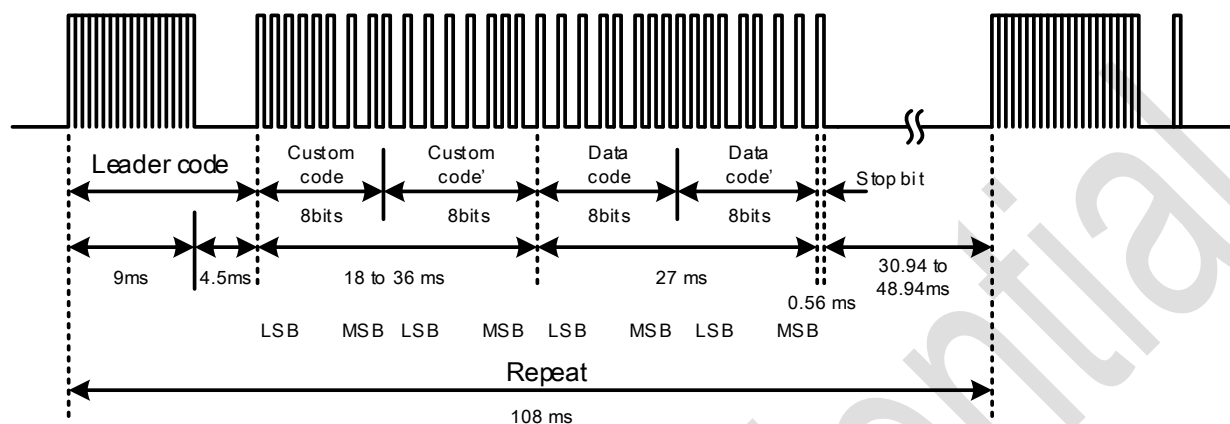


Figure 36. Waveform format of NEC code

RC5 code:

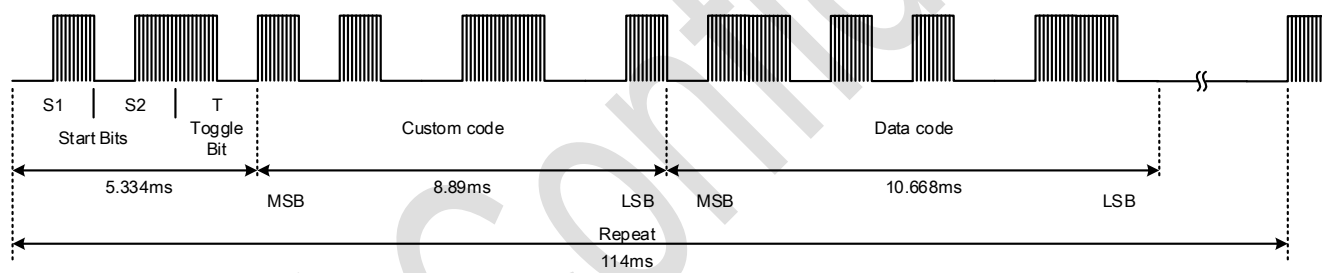


Figure 37. Waveform format of RC5 code

9.5.2 IR Receiver

SYD8811 offer Infrared receiver can detect level change of infrared signal. When detect a level change, the receiver will trigger an interrupt to report MCU that the signal's level and duration time prior to the signal change for algorithm learning.

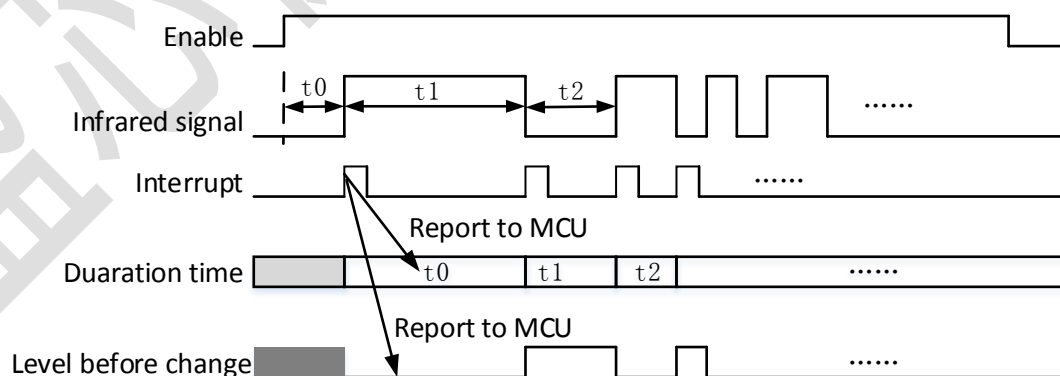


Figure 38. IR Receiver

10.0 Ordering information

Part number	Package	Packing	Minimum Order Quantity
SYD8811QN48	QFN 6mmx6mm 48-Pin	Tape Reel	3K
SYD8811QN32	QFN 5mmx5mm 32-Pin	Tape Reel	3K

Document Revision History

Revision Number	Date	Description
0.1	30 Aug 2018	1 st version;
1.0	06 Dec 2018	Update the pin assignment of QFN32 package;
1.1	02 Apr 2019	Update the 7816/IR part;
1.2	08 May 2018	Update the pin assignment of QFN32 package;

SYDTEK 盛芯微官方网站: <http://www.sydtek.com>

